

Reverse-domain superconductivity in superconductor–ferromagnet hybrids: effect of a vortex-free channel on the symmetry of $I - V$ characteristics

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We demonstrate experimentally that the presence of a single domain wall in an underlying ferromagnetic $\text{BaFe}_{12}\text{O}_{19}$ substrate can induce a considerable asymmetry in the current (I) – voltage (V) characteristics of a superconducting Al bridge. The observed diode-like effect, i.e. polarity-dependent critical current, is associated with the formation of a vortex-free channel inside the superconducting area which increases the total current flowing through the superconducting bridge without dissipation. The vortex-free region appears only for a certain sign of the injected current and for a limited range of the external magnetic field.

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The development of material deposition techniques and lithographic methods have made it possible to fabricate superconductor–ferromagnet (S/F) hybrid structures with controlled arrangements of ferromagnetic layers/elements.^{1–3} These flux- and exchange-coupled S/F hybrids^{2–5} are of fundamental interest for investigations of nontrivial interactions between superconductivity and nonuniform distributions of magnetization. In addition S/F hybrids seem to be potential candidates for the development of tunable elements of superconducting electronics.³

It is known that a nonuniform magnetic field can modify the conditions for the appearance of superconductivity due to the effect of a local field compensation.^{6,7} In flux-coupled S/F bilayers,³ the formation of localized superconductivity results in either domain-wall superconductivity (DWS) or reverse-domain superconductivity (RDS), when superconductivity occurs, respectively, above magnetic domain walls or above magnetic domains of opposite polarity with respect to the orientation of an external magnetic field H_{ext} (see review³ and references therein). The appearance of localized superconductivity (DWS and RDS) becomes possible if the amplitude of the nonuniform field, B_0 , is comparable or exceeds the upper critical field, H_{c2} , of the superconducting material, which was confirmed experimentally for various planar S/F structures.^{8–13}

A present challenge, associated with these S/F hybrids, is the direct investigation of the transport properties of superconducting channels that are induced by stray magnetic fields. Indeed, this problem seems to be crucial for any practical applications exploring the effect of localized superconductivity and guided vortex motion in tunable magnetic landscapes. Parallel magnetic domains in thick permalloy films were found to lead to a preferential vortex motion and a giant anisotropy of the critical currents in S films and crystals,^{14–18} even though the amplitude of the nonuniform field appears to be insufficient for the formation of localized superconductivity ($B_0/H_{c2} < 1$ at

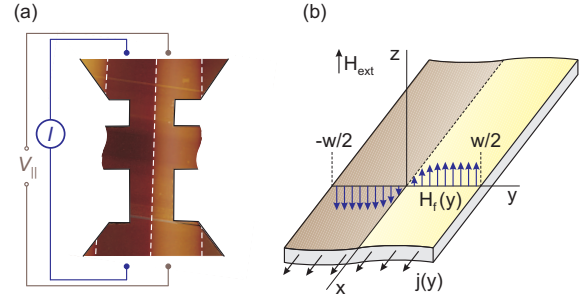


FIG. 1: (color online) (a) Combined magnetic and atomic force microscopy images of the hybrid sample. The dark and bright stripes, corresponding to the different ferromagnetic domains, are shown only within the cross-shaped superconducting bridge. White dashed lines depict the position of the domain walls. All elements of the electrical circuit is shown schematically. (b) The model S/F structure.

low temperatures).

It is important to note that the magnetic field induced by parallel magnetic domains in $\text{BaFe}_{12}\text{O}_{19}$ is rather high and thus suitable for RDS in superconducting Al films since $B_0/H_{c2} > 2.5$ for all temperatures.¹³ Using such S/F bilayers with well defined localized superconducting channels in a normal-metal matrix, we continue our previous study¹³ with the aim to test the potential of the superconducting channels to carry current. In this Letter we focus on the measurements of the current (I) – voltage (V) characteristics of a S/F bilayer along a *single* domain wall in a ferromagnetic substrate as a function of H_{ext} and analyze the dependence of the critical current I_c on H_{ext} for different signs of the bias current.

Our sample consists of a ferromagnetic crystal $\text{BaFe}_{12}\text{O}_{19}$ with a thin-film superconducting Al bridge grown on top. Since the ferromagnetic and superconducting parts were electrically isolated by a 5 nm Si buffer layer, the interaction between these parts was

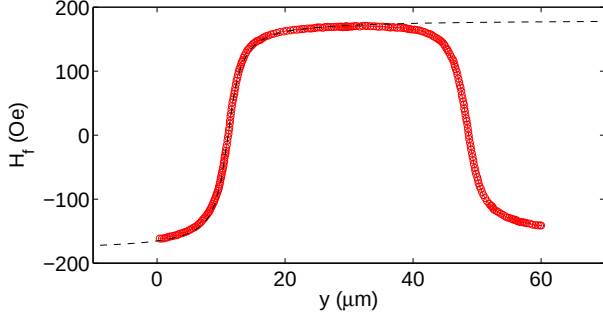


FIG. 2: (color online) The z -component of the field induced by the ferromagnetic domains, measured by a scanning Hall probe microscope along a line perpendicular to the domain walls at $T = 72$ K, $H_{ext} = 0$ and at height 400 nm. The dashed line corresponds to $H_f = H_0 \arctan(y/L)$ ($H_0 = 115$ Oe, $L = 1.5$ μm).

purely magnetostatic. Being cut along the proper crystallographic direction, the polished crystal $\text{BaFe}_{12}\text{O}_{19}$ exhibits a stripe-type domain structure with dominant in-plane magnetization.¹³ The location of the domain walls was determined by magnetic force microscopy, prior to the preparation of the superconducting bridge. The cross-shaped Al microbridge (30 μm wide and 50 nm thick) was fabricated by e-beam lithography, molecular beam epitaxy and lift-off etching [Fig. 1(a)]. A similar structure was used in Ref.¹³ for the observation of the anisotropy of the electrical resistance in this S/F bilayer.

The profile of the perpendicular z -component of the nonuniform magnetic field is shown in Fig. 2. Its amplitude, even though measured at a rather large distance (400 nm) from the surface, is close to the H_{c2} value for Al films ($H_{c2} \simeq 2 \cdot 10^2$ Oe at $T = 0$). Since the field amplitude inside the superconducting film, B_0 , will exceed H_{c2} at all temperatures, superconductivity appears in this S/F system only at $H_{ext} \neq 0$ as reverse-domain superconductivity above positively (negatively) magnetized domains at $H_{ext} < 0$ ($H_{ext} > 0$), respectively.

Figure 3 shows the typical $I - V$ characteristics measured at $T = 0.5$ K ($T/T_{c0} \simeq 0.34$). Depending on the H_{ext} value, there are three different cases:

- (i) symmetric normal-type $I - V$ dependence with almost constant slope dV/dI (not shown here);
- (ii) symmetric $I - V$ dependence with non-zero critical current (curves labelled 450 Oe and 470 Oe). This is realized in a rather wide H_{ext} range corresponding to the reverse-domain superconductivity;
- (iii) asymmetric hysteretic $I - V$ dependence (curves labelled 490 Oe and 510 Oe) with $I_c^{(+)} \neq I_c^{(-)}$. Here we introduce the critical currents $I_c^{(+)}$ and $I_c^{(-)}$ for the ascending branches of the $I - V$ curves both for positive (+) and negative (−) polarities of the transport current. This type of $I - V$ characteristics was found only in the close vicinity of the compensation field ($|H_{ext}| \simeq B_0$).

The dependencies of the critical currents $I_c^{(\pm)}$ on H_{ext}

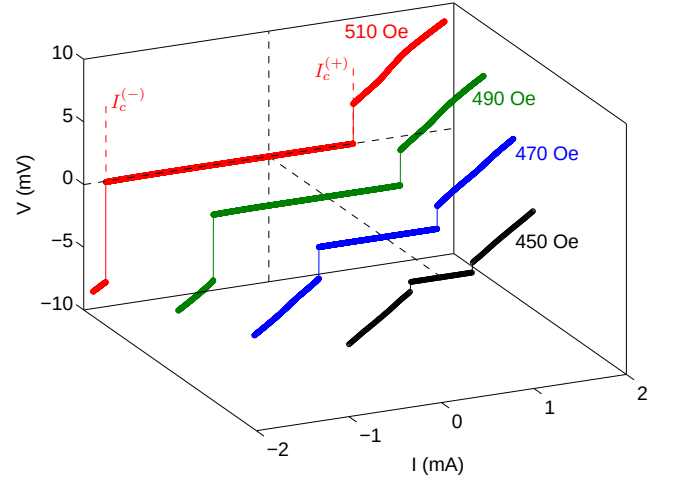


FIG. 3: (color online) Typical $I - V$ dependencies measured along the domain wall for different H_{ext} values. Both branches for $I > 0$ and $I < 0$ were measured starting from $I = 0$.

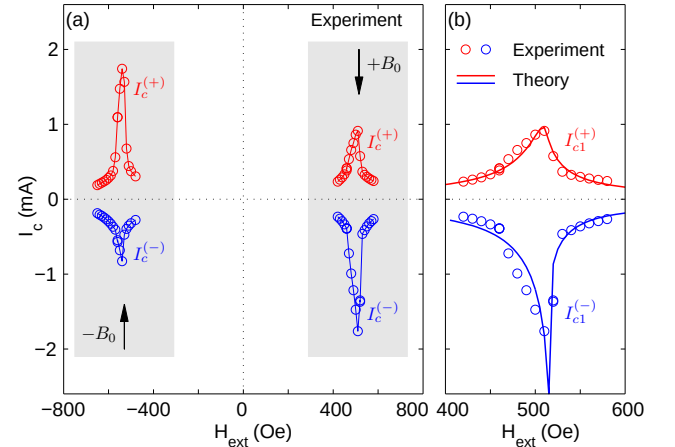


FIG. 4: (color online) (a) Critical currents $I_c^{(\pm)}$ as a function of H_{ext} at $T = 0.5$ K. The shaded areas correspond to the H_{ext} range where the decrease of the resistance from its normal value (i.e. the RDS regime) was detected. Arrows indicate the compensation field $|H_{ext}| = B_0$. (b) Comparison between experiment (circles) and theory (solid lines).

are summarized in Fig. 4(a). The relationship between $I_c^{(+)}$ and $I_c^{(-)}$ depends both on the absolute value of H_{ext} and its sign: $I_c^{(+)} > I_c^{(-)}$ at $H_{ext} < 0$ and vice versa. Thus, the most important finding of this paper is the field-induced change of the symmetry of the $I - V$ characteristics. The fact that the transmission capacity of the superconducting channel formed in the non-uniform magnetic field, can be strongly dependent on the polarity of the transport current may look rather unusual and counter-intuitive.

To clarify the physical origin of the difference between

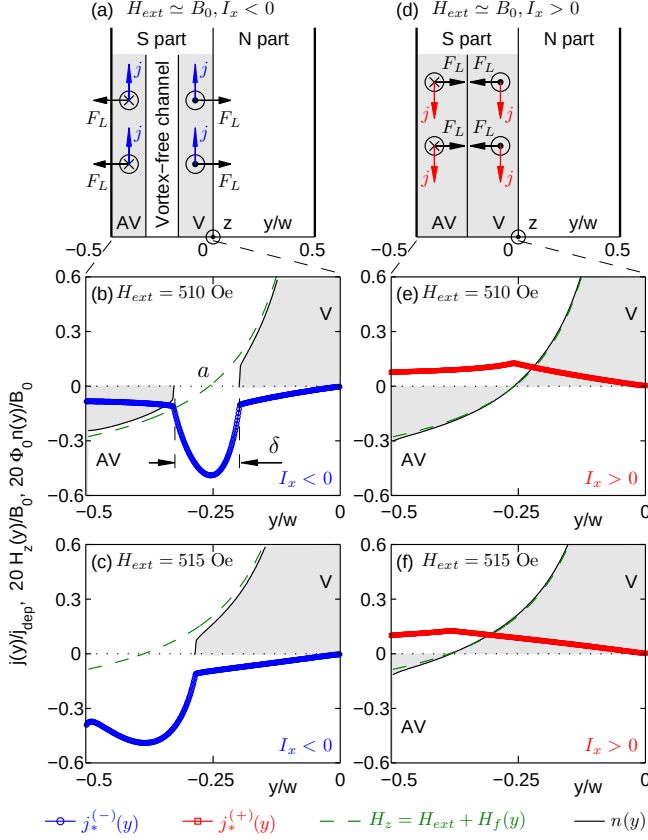


FIG. 5: (color online) Static vortex and current patterns in the S bridge in the presence of the non-uniform field $H_f = H_0 \arctan(y/L)$, corresponding to the maximum of the flowing current, at different H_{ext} values. V and AV stand for vortices and antivortices, j_{dep} is the depairing current density⁷. The right part of the superconducting bridge ($0 < y < w/2$) is in the normal state at $H_{ext} > 0$ and $j = 0$ and $n = 0$ there.

$I_c^{(+)}$ and $I_c^{(-)}$, we analyze the transport properties of the generic S/F bilayer within the London model. We consider a thin superconducting bridge (width w) in the field of a single straight domain wall positioned in the center of the bridge ($y = 0$) and aligned parallel to the x -axis [Fig. 1(b)]. We assume that all parameters of the resulting current/vortex structures depend only on the transverse y -coordinate. The current density $j(y)$ and vortex density $n(y)$ in the presence of a nonuniform field meet the Maxwell-London equation^{19,20}

$$\frac{4\pi\lambda^2}{c} \frac{dj}{dy} + \frac{d}{c} \int_{-w/2}^{w/2} \frac{j(y') dy'}{y' - y} = H_{ext} + H_f(y) - \Phi_0 n(y),$$

where $H_f(y) = H_0 \arctan(y/L)$ is the field induced by the domain wall, λ is the London penetration depth, d is the thickness of the superconductor, $\Phi_0 = \pi\hbar c/e$ is the flux quantum. To determine the critical current I_c

of the superconducting strip, corresponding to the transition between the state with motionless vortices to the flux motion regime, we apply the following conditions:

(i) the maximum of the current density in the vortex-free region should be equal to the critical current density j_s , which defines the threshold value for the nucleation of vortices and antivortices inside the superconductor or at its edges;

(ii) in order to guarantee a flux motion regime at $I = I_c$, $j(y)$ should be equal to the depinning current density j_p in the area where $n(y) \neq 0$, with $j_p = j_{p0}/(1 + |B_z|/B_p)$

$$j_p = \frac{j_{p0}}{(1 + |B_z|/B_p)}$$

(according to Kim-Anderson model²¹) and B_z

$$B_z = H_{ext} + H_f + \frac{d}{c} \int_{-w/2}^{w/2} \frac{j(y') dy'}{y - y'}$$

is the local magnetic field. As a result, in the vortex-free region, $n(y) = 0$, the current density can be larger than j_p .

(iii) the profile $j_*(y)$, which satisfies both conditions (i) and (ii), allows us to define the critical current as follows $I_c = \int_{-w/2}^{w/2} j_*(y) dy$.

In our calculations we use the parameters typical for our system: $w = 30 \mu\text{m}$, $d = 50 \text{ nm}$, $\lambda = 150 \text{ nm}$, $B_0 = 520 \text{ Oe}$, $B_p = 30 \text{ Oe}$, $H_0 = 331 \text{ Oe}$, $j_{p0} = 0.14 j_{dep}$, $j_s = 0.55 j_{dep}$, where j_{dep} is the depairing current density of Al at low temperatures.²² Our choice for the parameter $L = 0.35 \mu\text{m}$ seems to be reasonable since the width of the transient area in the B_z -distribution inside the superconducting film (at $h < 50 \text{ nm}$) can be substantially smaller than that measured at large distances ($L = 1.5 \mu\text{m}$ at $h = 400 \text{ nm}$). Since there is rather good agreement between the experimental data and the calculated dependencies $I_c^{(+)}(H_{ext})$ [Fig. 4(b)], we can interpret the asymmetry of the transmission capacity of the superconducting channels as follows.

Provided $H_{ext} \simeq B_0$, the magnetic field is effectively compensated in the left part of the bridge, while the right part will be switched to the normal state. Since the local field $H_z = H_{ext} + H_f$ changes its sign inside the superconducting area (in the case $H_{ext} < B_0$), the stable vortex structure should generally consist of vortices and antivortices. However the Lorentz force $\mathbf{F}_L = c^{-1} [\mathbf{j} \times \Phi_0]$ acting on a vortex depends on the direction of the transport current j , therefore the resulting vortex pattern, corresponding to the non-dissipative current flow, may be dependent on the sign of I_x . Indeed, an injection of the negative bias current ($I_x < 0$) forces vortices (antivortices) to move to the right (left), resulting in a vortex-free channel inside the RDS area [Fig. 5 (a1)–(c1)]. The exact position a and the width δ of such channel depends on H_{ext} . Since there are no vortices in a certain area, one can apply a larger current through such a vortex-free channel

without losing energy and the excess current due to this effect can be roughly estimated as $\delta \times (j_s - j_{p0})$. However, the vortex-free area is absent for a bias current of opposite polarity ($I_x > 0$), since vortices and antivortices move in counter directions and annihilate at the point of zero magnetic field [Fig. 5 (a2)–(c2)]. In this case the current density cannot be larger than j_{p0} and $I_c^{(+)} < I_c^{(-)}$. In the under-compensated regime, when the absolute H_{ext} value is substantially less than B_0 , the gradient of the local field $(dH_z/dy)_a$ increases rapidly as H_{ext} decreases [compare Fig. 5 (a1)–(c1)], $\delta \rightarrow 0$, and the diode effect vanishes. In the over-compensated regime ($H_{ext} > B_0$) the vortex-free region positioned near the left edge of the bridge becomes very narrow ($\delta \rightarrow 0$) and, as a consequence, the excess current goes to zero and the symmetry of the $I - V$ characteristics is restored. Obviously that for $H_{ext} < 0$ we have the same physics, but the excess current corresponds to the opposite case ($I > 0$)

and therefore $I_c^{(+)} > I_c^{(-)}$. All these conclusions are in agreement with our experimental observations [Fig. 4].

Summarizing, we showed that a nonuniform field can cause a pronounced asymmetry of the $I - V$ curves of a superconducting bridge provided $|H_{ext}| \simeq B_0$. The difference in the critical currents can be attributed to a removal of vortices from the inner part of the superconducting bridge under the action of the Lorentz force. Such a vortex-free channel, forming only for a certain polarity of the injected current, is able to carry extra current without dissipation and thus prevents the superconducting bridge from switching to the normal state.

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